

#### **Features**

- High Density Cell Desihn for Ultra Low R<sub>DS(on)</sub>
- · Fully Characterized Avalanche Voltage and Current
- Good Stability and Uniformity with High EAS
- · Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- · Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

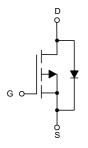
## **Maximum Ratings**

- Operating Junction Temperature Range: -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 0.847°C/W Junction to Case<sup>(Note 1)</sup>

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V <sub>DS</sub>	-60	V
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	- I <sub>D</sub>	-60	Α
	T <sub>C</sub> =100°C		-42.3	Α
Pulsed Drain Current		I <sub>DM</sub>	-260	Α
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	722	mJ
Total Power Dissipation		P <sub>D</sub>	177	W

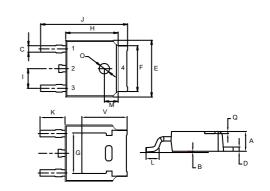
Note: 1.Surface Mounted on FR4 Board, t  $\leq$  10 sec. 2.T<sub>J</sub>=25°C,V<sub>DD</sub>=-30V,V<sub>G</sub>=-10V,L=0.5mH,R<sub>q</sub>=25 $\Omega$ .

#### **Internal Structure**



# P-CHANNEL MOSFET

# **DPAK(TO-252)**



- 1. Gate
- 2,4. Drain
  - 3. Source

DIMENSIONS					
INCHES		MM		NOTE	
DIM	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.1	14	2.9	90	TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.3	35	TYP.



## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

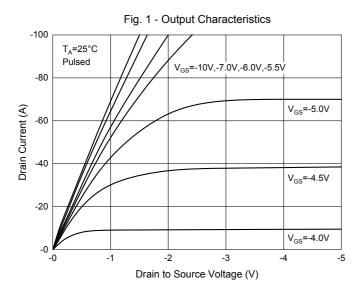
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics				1	1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-60			V
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}=0V, V_{GS}=\pm 20V$			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
Gate-Threshold Voltage <sup>(Note 3)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-2	-2.6	-3.5	V
Drain-Source On-Resistance (Note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A		13	18	mΩ
Forward Tranconductance <sup>(Note 3)</sup>	<b>g</b> <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A		25		S
Dynamic Characteristics(Note 4)				•		
Input Capacitance	C <sub>iss</sub>			5814		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-25V,V <sub>GS</sub> =0V,f=1MHz		483		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			234		
Total Gate Charge	Qg			75		
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =-30V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-20A		16		~C
Gate-Drain Charge	$Q_{gd}$			19		nC
Reverse Recovery Chrage	Q <sub>rr</sub>	I <sub>s</sub> =-20A, di/dt=-100A/µs		71		
Reverse Recovery Time	t <sub>rr</sub>	1 <sub>S</sub> =-20A, αι/αι=-100A/μS		49		
Turn-On Delay Time	t <sub>d(on)</sub>			18		
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =-30V, $R_{L}$ =1.5 $\Omega$ ,		20		ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{G}$ =3 $\Omega$		55		
Turn-Off Fall Time	t <sub>f</sub>			35		
Drain-Source Body Diode Cha	racteristi	cs	•	•	•	
Continuous Body Diode Current	I <sub>S</sub>	T <sub>C</sub> =25°C			-60	Α
Body Diode Voltage	V <sub>SD</sub>	I <sub>SD</sub> =-20A, V <sub>GS</sub> =0V			-1.2	V

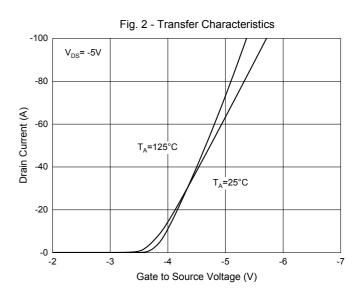
Note 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤2%.

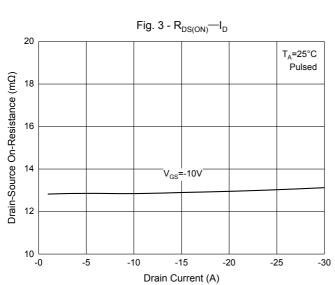
4. Guaranteed by Design, Not Subject to Production Testing.

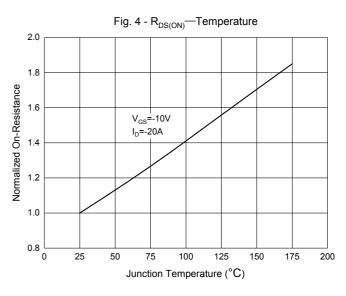


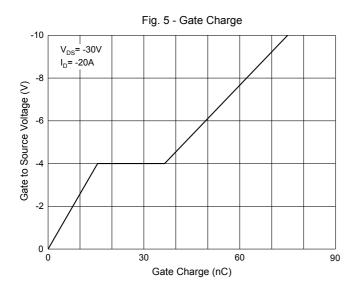
#### **Curve Characteristics**

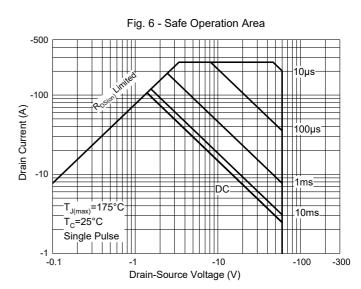














## **Curve Characteristics**

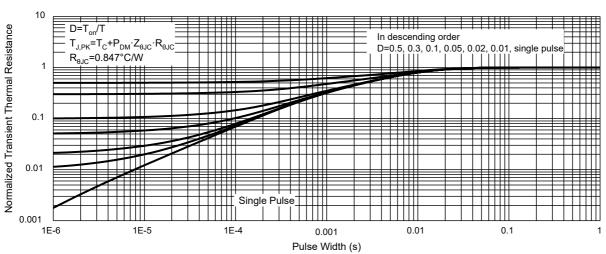


Fig. 7 - Normalized Transient Thermal Impedance



## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

Note: Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF

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